

# Interview Text Search

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1141	misfet.clm.	US-PGPUB; USPAT	OR	OFF	2006/08/29 17:51
L2	337196	(dram memory).clm.	US-PGPUB; USPAT	OR	OFF	2006/08/29 17:51
L3	517	capacitative.clm.	US-PGPUB; USPAT	OR	OFF	2006/08/29 17:52
L4	70855	(angstrom nanometer nm).clm.	US-PGPUB; USPAT	OR	OFF	2006/08/29 17:52
L5	984	2 same 4	US-PGPUB; USPAT	OR	OFF	2006/08/29 17:52
L6	0	5 same 3	US-PGPUB; USPAT	OR	OFF	2006/08/29 17:52
L7	1	5 and 3	US-PGPUB; USPAT	OR	OFF	2006/08/29 17:53
L8	10	5 and 1	US-PGPUB; USPAT	OR	OFF	2006/08/29 17:53

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	454	(ru ruthenium) same (nanometer nm angstrom) same cvd	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 17:35
L2	6519	(ruthenium Ru) and (titanium adj nitride TiN) and (titanium adj oxide TiO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57
L3	431336	(MIM M-I-M) (electrode and (insulate insulated insulating insulator insulater))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57
L4	2374	(MIM M-I-M) near3 capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57
L5	71	L2 and L4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 17:35
L6	4841	(257/296,306,310).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/29 16:57
L7	4265	L6 and (nm micron thick thickness thicknesses angstrom angstroms microns)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57
L8	70	L5 and (nm micron thick thickness thicknesses angstrom angstroms microns)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57

## EAST Search History

L9	4250	L7 not L8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57
L10	95	L6 and ruthenium with (nm micron thick thickness thicknesses angstrom angstroms microns)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57
L11	5667	(ru ruthenium) same (nanometer nm angstrom)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 17:34
L12	1450	(sputtering sputtering pcm) same cvd same (ru ruthenium pt platinum) same (nanometer nm angstrom thickness thick thin thinner thicker)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 17:01
L13	5	plug type bottom electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/08/29 16:57
L14	94	L10 not L8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57
L15	25	L12 and cup	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 16:57